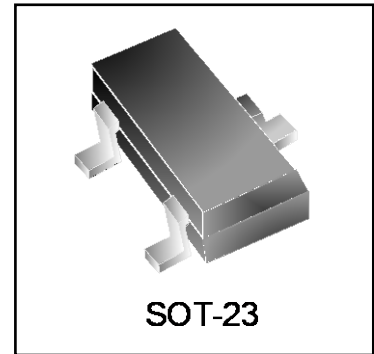


Features

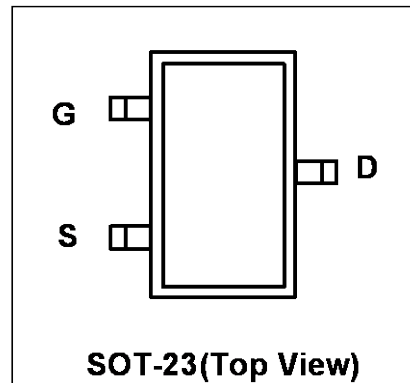
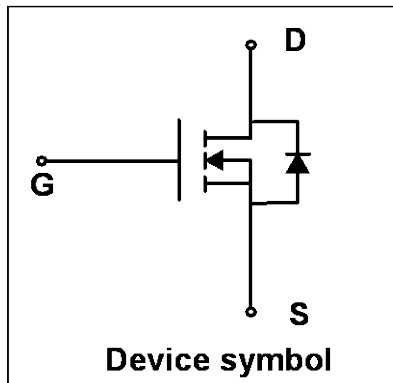
- Way-on Small Signal MOSFETs
- $V_{DS} = 30V$, $I_D = 5.8A$
 $R_{DS(on)} < 35m\Omega @ V_{GS} = 10V$
 $R_{DS(on)} < 40m\Omega @ V_{GS} = 4.5V$
 $R_{DS(on)} < 52m\Omega @ V_{GS} = 2.5V$
- Trench Power LV MOSFET Technology



Mechanical Characteristics

- SOT-23 Package
- Marking : Making Code
- RoHS Compliant

Schematic & PIN Configuration



Absolute Maximum Rating ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	5.8	A
	$T_C = 25^\circ C$		
Pulsed Drain Current ¹	I_{DM}	22	A
Power Dissipation	P_D	1.2	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction to Ambient ²	$R_{\theta JA}$	104	$^\circ C/W$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V _{GS} = 0V, I _D = 250μA	30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V _{DS} = 30V, V _{GS} = 0V	-	-	1	μA
Gate-body Leakage Current	I_{GSS}	V _{DS} = 0V, V _{GS} = ±12V	-	-	±100	nA
Gate Threshold Voltage	V_{GS(th)}	V _{GS} = 0V, I _D = 250μA	0.7	-	1.4	V
Drain-Source on-state Resistance ³	R_{DS(on)}	V _{GS} = 10V, I _D = 5.8A	-	23	35	mΩ
		V _{GS} = 4.5V, I _D = 5A	-	26	40	
		V _{GS} = 2.5V, I _D = 4A	-	40	52	
Dynamic Characteristics⁴						
Input Capacitance	C_{iss}	V _{GS} = 0V, V _{DS} = 15V, f = 1MHz	-	560	-	pF
Output Capacitance	C_{oss}		-	70	-	
Reverse Transfer Capacitance	C_{rss}		-	50	-	
Switching Characteristics⁴						
Total Gate Charge	Q_g	V _{DS} = 15V, V _{GS} = 4.5V, I _D = 5.8A	-	7.5	-	nC
Gate-Source Charge	Q_{gs}		-	1.6	-	
Gate-Drain Charge	Q_{gd}		-	2.1	-	
Turn-on Delay Time	t_{d(on)}	V _{DS} = 15V, V _{GS} = 10V, R _{GEN} = 3Ω, R _L = 2.7Ω	-	5	-	ns
Turn-on Rise Time	t_r		-	7	-	
Turn-off Delay Time	t_{d(off)}		-	40	-	
Turn-off Fall Time	t_f		-	6	-	
Source-Drain Body Diode Characteristics						
Body Diode Voltage ³	V_{SD}	I _S = 1A, V _{GS} = 0V	-	-	1.3	V
Continuous Source Current	I_S		-	-	5.8	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)} = 150°C
2. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
3. Pulse Test: Pulse width ≤ 300μs, duty cycle ≤ 2%.
4. This value is guaranteed by design hence it is not included in the production test

Typical Characteristics

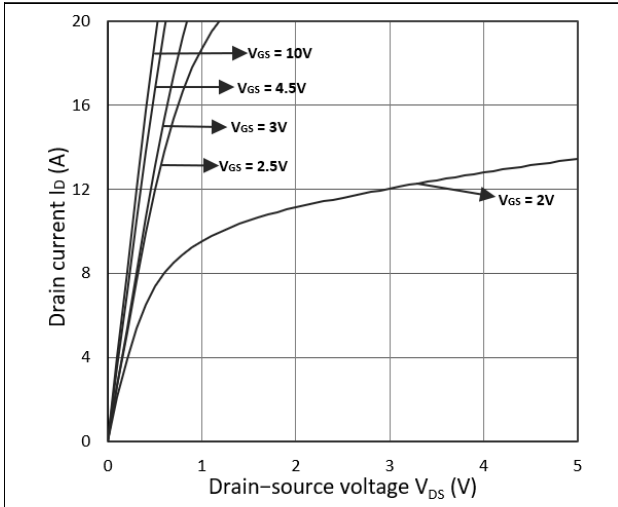


Figure 1. Output Characteristics

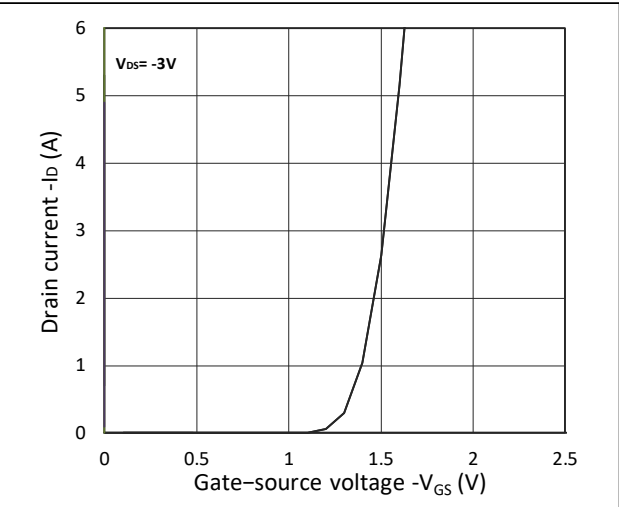


Figure 2. Transfer Characteristics

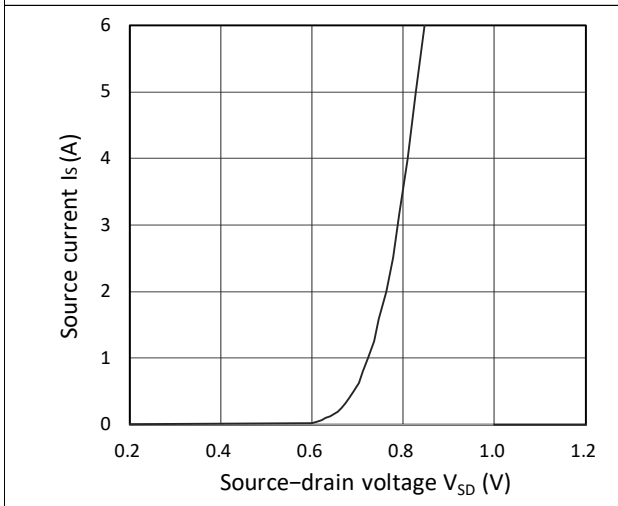


Figure 3. Forward Characteristics of Reverse

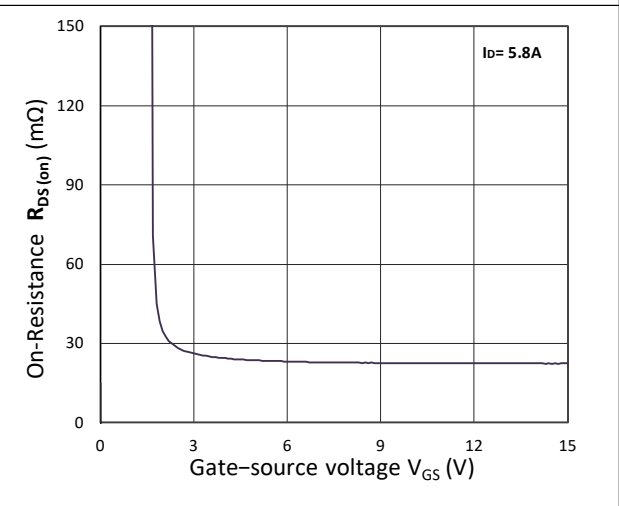


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

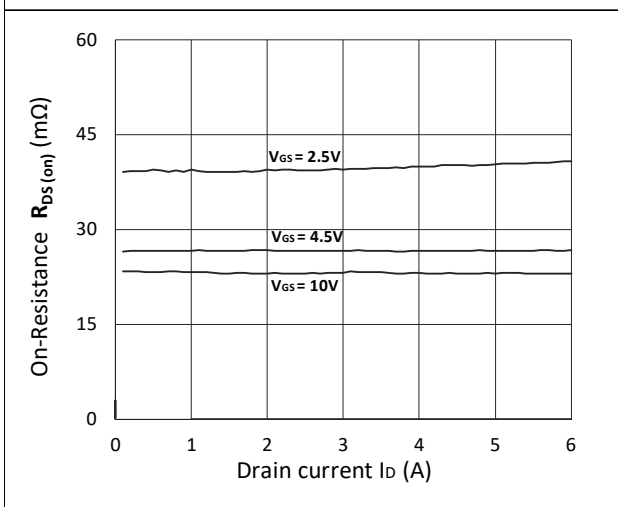


Figure 5. $R_{DS(ON)}$ vs. I_D

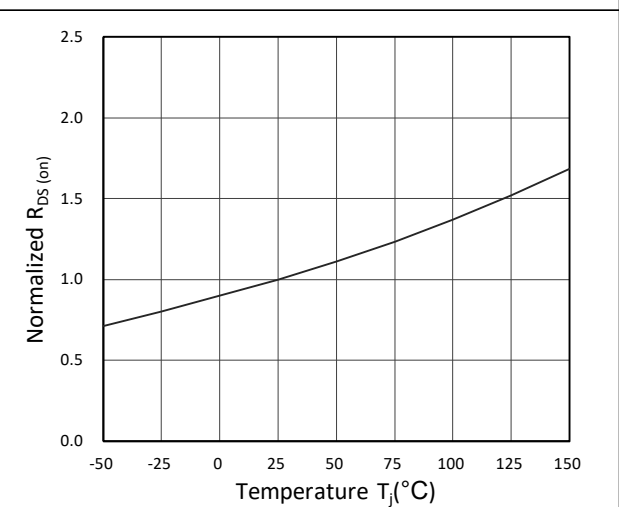


Figure 6. Normalized $R_{DS(ON)}$ vs. Temperature

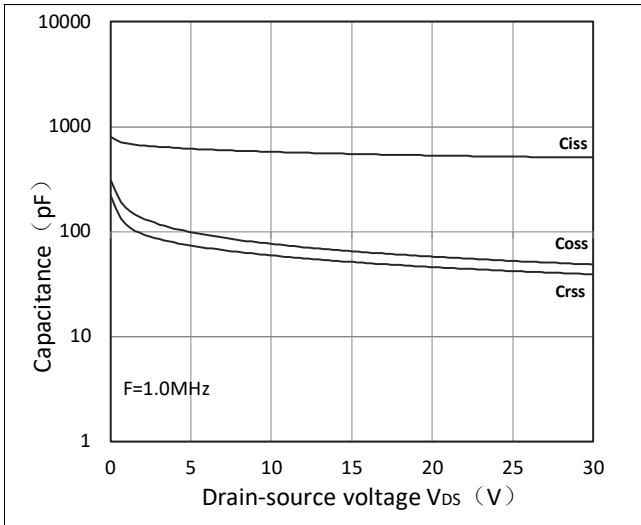


Figure 7. Capacitance Characteristics

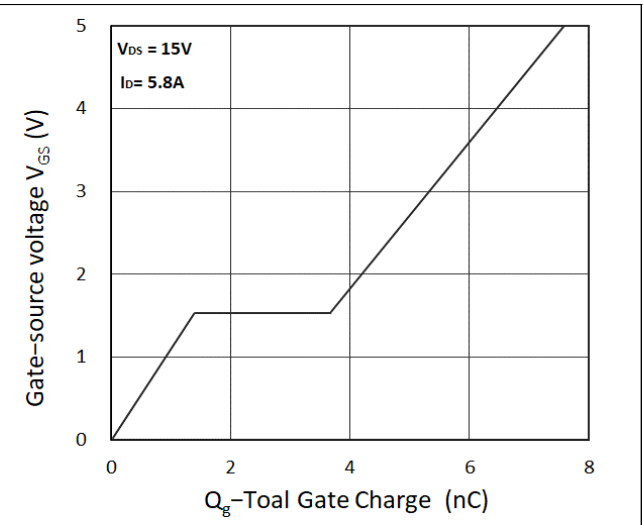
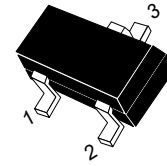
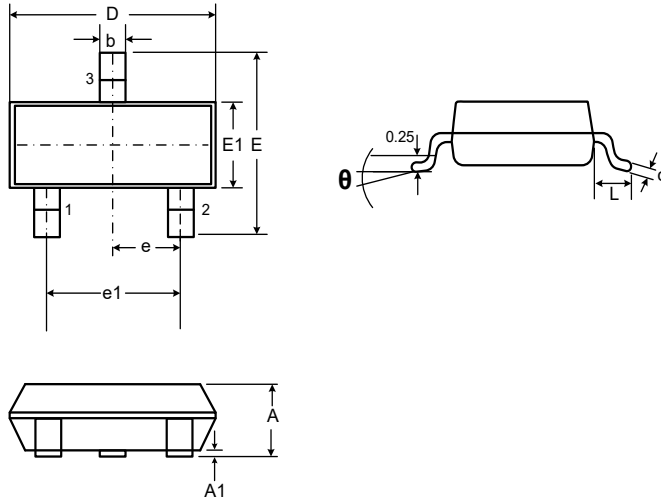


Figure 8. Gate Charge Characteristics

Outline Drawing – SOT-23

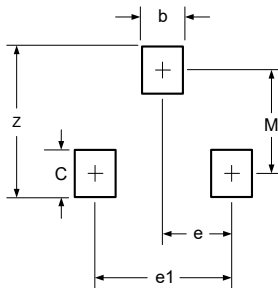
PACKAGE OUTLINE



SOT-23

DIMENSIONS

SYMBOL	MILLIMETER		INCHES	
	MIN	MAX	MIN	MAX
A	0.90	1.15	0.035	0.045
A1	0.00	0.10	0.000	0.004
b	0.30	0.50	0.012	0.020
c	0.08	0.15	0.003	0.006
D	2.80	3.00	0.110	0.118
E	2.25	2.55	0.089	0.100
E1	1.20	1.40	0.047	0.055
e	0.95 BSC		0.037BSC	
e1	1.80	2.00	0.071	0.079
L	0.55REF		0.022REF	
θ	0°	8°	0°	8°



DIMENSIONS		
DIM	INCHES	MILLIMETERS
M	0.080	2.02
C	0.032	0.80
Z	0.111	2.82
e	0.037 BSC	0.95 BSC
e1	0.075 BSC	1.90 BSC
b	0.032	0.80

Notes

1. Dimensioning and tolerances per ANSI Y14.5M, 1985.
2. Controlling Dimension: Inches
3. Pin 3 is the cathode (Unidirectional Only).
4. Dimensions are exclusive of mold flash and metal burrs.

Marking Codes

Part Number	WM03N58M
Marking Code	

Package Information

Qty: 3k/Reel

CONTACT INFORMATION

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WAYON website: <http://www.way-on.com>

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[STF5N65M6](#) [IRF40H233XTMA1](#) [STU5N65M6](#) [DMN6022SSD-13](#) [DMN13M9UCA6-7](#) [DMTH10H4M6SPS-13](#) [IPS60R360PFD7SAKMA1](#)
[DMN2990UFB-7B](#) [SSM3K35CT,L3F](#) [IPLK60R1K0PFD7ATMA1](#) [2N7002W-G](#) [MCAC30N06Y-TP](#) [IPWS65R035CFD7AXKSA1](#)
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[PJMF280N60E1_T0_00201](#) [PJMF600N65E1_T0_00201](#) [PJMF900N65E1_T0_00201](#)